

1 SEMICONDUCTOR CURRENT  
2 DETECTOR OF IMPROVED  
3 NOISE IMMUNITY  
4

5 BACKGROUND OF THE INVENTION  
6

7 This invention relates to current detectors, more specifically to  
8 that employing a semiconductor Hall-effect device for obtaining a voltage  
9 proportional to the magnitude of the current detected. Still more specifi-  
10 cally, the invention deals with how to improve the noise immunity of this  
11 kind of current detector.

12 By the term "Hall-effect device" used herein and in the claims  
13 appended hereto is meant the voltage generator built on the familiar Hall  
14 effect to give an output voltage in direct proportion to the magnetic  
15 field applied. Disposed contiguous to a current path, the Hall-effect de-  
16 vice will be subjected to the magnetic field that is generated in propor-  
17 tion to the magnitude of the current flowing through the path. The  
18 result will be the production of a voltage proportional to the current  
19 magnitude.

20 The instant applicant proposed in PCT/JP99/05408 a current detec-  
21 tor in which an insulating film is formed upon a semiconductor Hall-effect  
22 device and, on this insulating film, a conductor layer for carrying a cur-  
23 rent to be detected. The current path is thus situated as close as fea-  
24 sible to the Hall-effect device, resulting in enhancement of the sensitivity  
25 of the current detector.

26 This prior art current detector proved to be unsatisfactory, how-  
27 ever, in its noise immunity. It was equipped with no means designed  
28 explicitly for protection of the device against production of spurious volt-  
29 age signals due to external disturbances.

30 SUMMARY OF THE INVENTION  
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32  
33 The present invention seeks to enhance the noise immunity, and  
34 hence the reliability of operation, of the current detector of the type  
35 defined.

36 Stated in brief, the invention concerns a semiconductor current de-

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1 tector comprising a semiconductor substrat having a Hall-effect device  
2 formed therein from one surface thereof, the Hall-effect device having a  
3 plurality of semiconductor regions including a primary working region for  
4 generating a Hall voltage proportional to the magnitude of a current or  
5 to be detected or measured. A conductor strip is formed over said one  
6 surface of the semiconductor substrate via insulating means so as to  
7 extend around at least part of the primary working region of the Hall-ef-  
8 fect device, for carrying at least a prescribed fraction of the current to  
9 be translated into the Hall voltage. A shielding layer is formed in the  
10 insulating means for shielding the Hall-effect device from external disturb-  
11 ances.

12 Typically, the insulating means is a lamination of three insulating  
13 layers. Electrodes, as well as conductor strips joined thereto, are formed  
14 on a first insulating layer which directly overlies the semiconductor sub-  
15 strate. The shielding layer is formed on part of a second insulating lay-  
16 er which overlies the first insulating layer. The conductor strip is  
17 formed on a third insulating layer overlying the second insulating layer.

18 The above arrangement of the three insulating layers in relation  
19 to the shielding layer and other components of the current detector is  
20 not a requirement. Alternatively, for instance, the shielding layer may be  
21 provided on the third insulating layer, and the conductor strip between  
22 the second and the third insulating layer. As a further alternative, a  
23 fourth insulating layer may be provided over the third insulating layer,  
24 and a second shielding layer on this fourth insulating layer.

25 Shielded by one or more shielding layers as above, the current  
26 detector will detect currents without errors due to external disturbances.  
27 The shielding layer or layers, as well as the current-carrying conductor  
28 strip, are integrally built into the semiconductor current detector, so that  
29 no substantial increase in size results from the addition of the shielding  
30 layer or layers. The integration of the conductor strip with the Hall-  
31 effect device is desirable by reason of their unvarying positional stabili-  
32 ty, and hence a consistently high accuracy of detection, from one current  
33 detector to another.

34 The above and other objects, features and advantages of the in-  
35 vention and th manner of realizing them will become more apparent, and  
36 the invention itself will best be understood, from the foll wing description

1 taken together with the attached drawings showing the preferred embodi-  
2 ments of the invention.

#### 3 4 *BRIEF DESCRIPTION OF THE DRAWINGS*

5  
6 FIG. 1 is a plan view of the current detector embodying the prin-  
7 ciples of the instant invention, the view not showing the fourth insulat-  
8 ing layer and the magnetic collector, and showing the encapsulation in  
9 phantom outline, to reveal other parts;

10 FIG. 2 is a section through the current detector, taken along the  
11 line A-A in FIG. 1;

12 FIG. 3 is a plan view of the Hall-effect device included in the  
13 FIG. 1 current detector;

14 FIG. 4 is a plan view of the insulating plate, together with the  
15 bottom shielding layer thereon, included in the FIG. 1 current detector;

16 FIG. 5 is a plan view showing the sheet-metal baseplate, pair of  
17 current-path terminals, and other terminals of the FIG. 1 current detector  
18 in their relative positions;

19 FIG. 6 is a plan view of a sheet-metal punching for use in the  
20 fabrication of the baseplate and terminals shown in FIG. 5;

21 FIG. 7 is a plan view showing the semiconductor substrate of the  
22 FIG. 1 current detector on a slightly enlarged scale;

23 FIG. 8 is an enlarged, fragmentary section through the Hall-effect  
24 device of the FIG. 1 current detector, taken along the line B-B in FIG.  
25 1;

26 FIG. 9 is a view similar to FIG. 1 but showing an alternative em-  
27 bodiment of the invention;

28 FIG. 10 is an enlarged, fragmentary section through the Hall-effect  
29 device of the FIG. 9 current detector, taken along the line C-C in FIG.  
30 9; and

31 FIG. 11 is a view similar to FIG. 10 but showing another alterna-  
32 tive embodiment of the invention.

#### 33 34 *DESCRIPTION OF THE PREFERRED EMBODIMENTS*

35  
36 The general organization of the first preferred form of current

1 detector according to the invention will become apparent from a study of  
2 FIG. 1 and 2. The current detector comprises:

3 1. a semiconductor Hall-effect device 1 for providing an output  
4 voltage indicative of the magnitude of a current  $I_s$  to be detected or  
5 measured;

6 2. a metal-made baseplate 2 mechanically supporting the Hall-effect  
7 device;

8 3. two current path terminals 3 and 4 for the inflow and outflow,  
9 respectively, the current  $I_s$

10 4. four lead terminals 6, 7, 8 and 9 for connection of the Hall-ef-  
11 fect device 1 to external circuits;

12 5. two other terminals 10 and 11 for grounding the baseplate 2;

13 6. a wire or like conductor 12 bridging the current path termi-  
14 nals 3 and 4 for providing a first current path from the former to the  
15 latter for carrying a first fraction  $I_{s1}$  of the current  $I_s$ ;

16 7. two other wires or like conductors 13 and 14 and a strip 15 of  
17 conductor layer conjointly providing a second current path from the cur-  
18 rent path terminal 3 to 4 for carrying a second fraction  $I_{s2}$  of the cur-  
19 rent  $I_s$ , which fraction is to be translated into a voltage signal by the  
20 Hall-effect device 1;

21 8. an insulating plate 16 between Hall-effect device 1 and base-  
22 plate 2;

23 9. a first or bottom shielding layer 17 between Hall-effect device  
24 1 and insulating plate 16;

25 10. a second or top shielding layer 50 overlying the Hall-effect  
26 device 1;

27 11. a magnetic collector 51 further overlying the top shielding layer  
28 50; and

29 12. a plastic encapsulation 18 enclosing all of the current detector  
30 but parts of the noted terminals 3, 4 and 6-11.

31 As depicted by itself in FIG. 3, the Hall-effect device 1 is of  
32 generally rectangular shape as seen in a plan view as in this figure, and  
33 has four electrodes 19a, 20a, 21a and 22a near its geometric center.  
34 These electrodes 19a-22a are connected via conductor strips 19b-22b to  
35 terminals 19c-22c, respectively, of the Hall-effect device.

36 The Hall-effect device 1 is to be put to use with the terminals

1 19c and 20c connected to an external circuit, not shown, for inputting a  
2 control current, and with the terminals 21c and 22c connected to an ex-  
3 ternal differential amplifier, also not shown, for putting out the Hall volt-  
4 age. The control current input terminals 19c and 20c, and therefore the  
5 electrodes 19a and 20a, are connected respectively to a pair of semicon-  
6 ductor regions 24 and 25, FIG. 7, of a semiconductor substrate 23 in  
7 which the device is formed. The voltage output terminals 21c and 22c,  
8 and therefore the electrodes 21a and 22a, are connected respectively to  
9 semiconductor regions 26 and 27 of the substrate 23.

10 With reference to both FIGS. 7 and 8 the semiconductor substrate  
11 23 is a generally rectangular piece of silicon, having four other regions  
12 28-31 than the four aforementioned regions 24-27 of *n* conductivity type.  
13 Of *n* conductivity type, the fifth semiconductor region 28 takes the form  
14 of an island of cross shape, as seen in a plan view as in this figure, in  
15 the middle of the *p*-type eighth semiconductor region 31 which occupies  
16 most part of the semiconductor substrate 23.

17 The noted first and second semiconductor regions 24 and 25 are  
18 of  $n^+$  type, higher in impurity concentration than the fifth semiconductor  
19 region 28, and are formed as islands, spaced from each other along the *y*  
20 axis in FIG. 7, in the fifth semiconductor region 28. The first and sec-  
21 ond electrodes 19a and 20a are in ohmic contact with these semiconductor  
22 regions 24 and 25. When the unshown control current supply circuit is  
23 connected to the input terminals 19c and 20c, the control current  $I_c$  is to  
24 flow across the fifth semiconductor region 28, either from the first 24 to  
25 the second 25 semiconductor region or the other way around.

26 Of  $n^+$  type, with an impurity concentration higher than that of  
27 the fifth semiconductor region 28, the third and fourth semiconductor re-  
28 gions 26 and 27 lie approximately centrally of the fifth semiconductor  
29 region 28 in the direction of the *y* axis, with a spacing from each other  
30 in the direction of the *x* axis. The semiconductor regions 26 and 27  
31 are partly contiguous to the fifth semiconductor region 28, partly to the  
32 *p* type sixth and seventh semiconductor regions 29 and 30, and are in  
33 ohmic contact with the third and fourth electrodes 21a and 22a. The  
34 semiconductor regions 29 and 30 are intended to reduce the area of con-  
35 tact of the semiconductor regions 26 and 27 with the semiconductor re-  
36 gion 28.

1           The Hall voltage is to be obtained between the third and fourth  
2 semiconductor regions 26 and 27 when the control current  $I_c$  is made to  
3 flow across the semiconductor region 28 from the first 24 to the second  
4 25 semiconductor region, with a magnetic field perpendicular to the direc-  
5 tion of current flow. Therefore, the term "primary working region" of  
6 the Hall-effect device, as used herein and in the claims appended hereto,  
7 may be construed as the fifth semiconductor region 28 or, more strictly,  
8 that part of the region 28 which lies intermediate the semiconductor re-  
9 gions 24 and 25 and intermediate the semiconductor regions 26 and 27.

10           As indicated in both FIGS. 2 and 8, the semiconductor substrate  
11 23 has a laminar insulation 32 formed on its top surface, as seen in this  
12 figure, and a layer 33 of aluminum or like metal formed on its bottom  
13 surface. The laminar insulation 32 is shown to be composed of three  
14 layers or laminae 32a, 32b and 32c of silicon oxides and another layer  
15 32d of adhesive material in this embodiment of the invention.

16           It has been stated with reference to FIG. 3 that the electrodes  
17 19a-22a are connected via the conductor strips 19b-22b to the terminals  
18 19c-22c, respectively, of the Hall-effect device. As will be understood  
19 from both FIGS. 1 and 2, the conductor strips 19b-22b, typically of alumi-  
20 num, have parts sandwiched between the insulating layers 32a and 32b.  
21 The ends of these parts contact the semiconductor regions 24-27 through  
22 windows in the insulating layer 32a. The other ends of the conductor  
23 strips 19b-22b are connected to the terminals 19c-22c through windows in  
24 the other insulating layers 32b and 32c.

25           With reference to FIGS. 1-3 and 8 the top shielding layer 50 is a  
26 layer of electroconductive material such as molybdenum, formed on the  
27 second insulating layer 32b as by vapor deposition, sputtering, or plating.  
28 The top shielding layer 50 is so sized and positioned as to cover at  
29 least the semiconductor region 28, as seen in a plan view as in FIGS. 1  
30 and 3, and electrically connected to the Hall-effect device terminal 22c  
31 which is grounded. Formed by vapor deposition or sputtering, the third  
32 insulating layer 32c overlies the top shielding layer 50.

33           The conductor strip 15 for carrying the current fraction  $I_{s2}$ , set  
34 forth with reference to FIG. 1, is formed on the third insulating layer  
35 32c. Preferably, the conductor strip 15 is fabricated from gold by plat-  
36 ing, vapor deposition, or sputtering to a thickness of from about five to

1 thirteen micrometers. The fourth insulating layer 32d is formed on the  
2 third insulating layer 21c following the formation of the conductor strip  
3 15 thereon.

4 Overlying the fourth insulating layer 32d is the magnetic collector  
5 51 which is of magnetic material in sheet form that is higher in magnetic  
6 permeability than air, examples being ferrite, iron, and nickel. The mag-  
7 netic collector 51 is attached to the fourth insulating layer 32d, which is  
8 of a synthetic adhesive, so as to cover at least all of the semiconductor  
9 region 28 as seen from above in FIG. 8. Alternatively, however, the  
10 magnetic collector could be a film of magnetic material formed on the  
11 insulating layer 32d as by vapor deposition or coating.

12 FIG. 5 best indicates that the metal-made baseplate 2 is approxi-  
13 mately square in shape and, as clearly revealed in FIG. 2, somewhat larg-  
14 er in size than the Hall-effect device 1. The baseplate 2 is designed to  
15 serve not only as mechanical support for the Hall-effect device 1 but as  
16 heat radiator and, further, as electrostatic shield. For successful fulfill-  
17 ment of all such intended functions the baseplate 2 may be fabricated  
18 from sheet copper of 0.5 to 1.0 millimeter in thickness with a nickel plat-  
19 ing thereon.

20 The two terminals 10 and 11 extend from the pair of opposite  
21 edges of the baseplate 2 for grounding. The current path terminals 3  
22 and 4 extend along one of the other two opposite edges of the baseplate  
23 2, with spacings therefrom and a spacing from each other. The terminals  
24 6-9 for connection of the Hall-effect device to external circuits are also  
25 spaced from the baseplate 2. Mechanically, however, the Hall-effect de-  
26 vice 1 and the terminals 3, 4, 6-11 are all firmly interconnected by the  
27 plastic encapsulation 18, indicated in phantom outline in FIG. 5, closely  
28 enveloping the complete current detector, leaving exposed parts of these  
29 terminals.

30 The baseplate 2 and the terminals 3, 4 and 6-11 can all be fab-  
31 ricated from a sheet-metal punching shown in FIG. 6 and therein general-  
32 ly designated 40. The punching 40 has a frame portion 41 holding the  
33 terminals 3, 6, 8 and 10 in their prescribed relative positions, another  
34 frame portion 42 likewise holding the terminals 4, 7, 9 and 11, and still  
35 another frame portion 43 interconnecting the foregoing two frame portions  
36 41 and 42. All the terminals 3, 4 and 6-11 are to be cut off the frame





1 Hall-effect device 1 are wired at 36-39, FIG. 1, to the lead terminals 6-9,  
2 respectively, of the current detector.

3 Typically made from aluminum, the wire 12 interconnecting the cur-  
4 rent path terminals 3 and 4 is for formation of the first, direct current  
5 path from terminal 3 to terminal 4. This first current path is to carry  
6 the first fraction  $I_{s1}$  of the current  $I_s$  to be detected or measured, as  
7 that current is divided into the two fractions  $I_{s1}$  and  $I_{s2}$  at the end of  
8 the terminal 3. A description of the second, indirect current path from  
9 terminal 3 to terminal 4, for carrying the second current fraction  $I_{s2}$  to  
10 be actually translated into a voltage output by the Hall-effect device 1,  
11 follows.

12 As seen in FIGS. 1, 3, 7 and 8, the conductor strip 15 of alumi-  
13 num or the like is formed on the insulating layers 32 so as to surround,  
14 as seen in a plan view, the semiconductor region 28, the main working  
15 part, in the broader sense of the term, of the Hall-effect device 1. The  
16 conductor strip 15 should surround at least about three quarters, prefera-  
17 bly ninety-five percent or so, of the periphery of the main working part  
18 of the Hall-effect device 1.

19 The conductor strip 15 has one extremity thereof coupled to the  
20 first current path terminal 3 via the aluminum wire 13, and the other  
21 extremity thereof coupled to the second current path terminal 4 via the  
22 aluminum wire 14, thereby completing the second current path, which is  
23 in parallel with the first current path, for carrying the second current  
24 fraction  $I_{s2}$  from terminal 3 to terminal 4 via the Hall-effect device 1.  
25 So arranged and electrically connected to the current path terminals 3  
26 and 4, the conductor layer 15 is designed to apply to the Hall-effect  
27 device 1 the magnetic flux due to the flow of the second current frac-  
28 tion  $I_{s2}$  therethrough.

### 30 Operation

31  
32 Let us assume that the resistances of the two current path termi-  
33 nals 3 and 4 are negligibly small. Then the current fractions  $I_{s1}$  and  $I_{s2}$   
34 divided between the two current paths are defined as:

35  
36 
$$I_{s1} = I_s [ R_2 / (R_1 + R_2) ]$$

1 
$$I_{s2} = I_s [ R_1 / (R_1 + R_2) ]$$

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3 where

4  $R_1$  = the resistance of the wire 12 throughout its length,

5  $R_2$  = the resistance of the total length of the wire 13, the con-  
6 ductor layer 15 and the wire 14.

7 For detection or measurement of the current  $I_s$  flowing through  
8 some electric circuit under measurement, by the current detector of the  
9 above described construction, the current path terminals 3 and 4 may be  
10 serially connected to the desired electric circuit. The lead terminals 6  
11 and 7 may be connected to the unshown control current supply circuit  
12 for causing the control current  $I_c$ , FIG. 7, to flow between the semicon-  
13 ductor regions 24 and 25, and the other lead terminals 8 and 9 to the  
14 unshown amplifier for applying thereto the Hall voltage indicative of the  
15 magnitude of the current  $I_s$ .

16 Flowing into the current detector from the current path terminal 3,  
17 the current  $I_s$  to be measured will be divided into  $I_{s1}$  and  $I_{s2}$ . The  
18 first fraction  $I_{s1}$  will flow from terminal 3 to terminal 4 by way of the  
19 wire 12, the first current path. The second fraction  $I_{s2}$  will flow from  
20 terminal 3 to terminal 4 by way of the second path constituted of the  
21 wire 13, conductor strip 15, and wire 14. As the second fraction  $I_{s2}$   
22 flows through the conductor strip 15 around the main working part of the  
23 Hall-effect device 1, the magnetic field  $H$  will be generated which, accord-  
24 ing to the Ampere rule, is oriented in the direction indicated by the  
25 broken-line arrows in FIG 8. This direction of the magnetic field is  
26 perpendicular to the direction of the control current  $I_c$  in the semicon-  
27 ductor region 28, so that the Hall voltage will be generated between the  
28 semiconductor regions 26 and 27, hence between the electrodes 21 and 22,  
29 and hence between the lead terminals 8 and 9. The Hall voltage is pro-  
30 portional to the strength of the magnetic field  $H$ , which in turn is pro-  
31 portional to the magnitude of the current  $I_s$ , so that this current is de-  
32 tectable from the Hall voltage.

33 The advantages gained by the above described embodiment of the  
34 invention may be summarized as follows:

35 1. The top shielding layer 50 thoroughly covers the top side of  
36 most of the Hall-effect device 1 notably including its primary working

part, the semiconductor region 28, so that the voltage across this semiconductor region as detected by the pair of electrodes 21a and 22a is protected against spurious variations due to external disturbances.

2. The baseplate 2 and conductive bonding agent layer 35a serve conjointly to shield the bottom side of the Hall-effect device 1, making the device all the more immune to inductive and other noise.

3. The shielding layer 50 is compactly sandwiched between the insulating laminae 32b and 32c on the semiconductor substrate 23.

4. The magnetic collector 51 makes it possible for the magnetic flux, created by current flow through the conductor strip 15, to be directed most efficiently into the semiconductor region 28, with the consequent enhancement of the efficiency of current detection.

5. Directly overlying the insulating layers 32 on the surface of the semiconductor substrate 23, the conductor strip 15 for carrying the current fraction  $I_{s2}$  is situated as close as practical to the Hall-effect device 1 formed in the substrate, again for higher detection sensitivity.

6. As the conductor strip 15 surrounds some ninety-five percent of the periphery of the Hall-effect device 1, the magnetic lines of force will act on the semiconductor region 28 from all of its four sides, giving still another cause for enhanced sensitivity.

7. All but parts of the terminals 3, 4 and 6-11 of the current detector is encapsulated for greater structural stability and operational reliability.

8. The current  $I_s$  is not directly detected but in terms of its division  $I_{s2}$  directed through the conductor strip 15 on the semiconductor substrate 23. Therefore, if the ratio of  $R_1$  to  $R_2$  is set at one to nine, for instance, then the current  $I_{s2}$  actually flowing through the conductor strip 15 can be as small as 10 amperes when the current  $I_s$  to be detected is 100 amperes.

9. The wire 12 providing the first current path, and the wires 13 and 14 and the conductor strip 15 providing the second current path, are both enclosed in one and the same plastic package 18. The temperature difference between the two current paths is thus reduced to a minimum, as are variations in the relative magnitudes of the currents  $I_{s1}$  and  $I_{s2}$  due to the temperature difference.

10. The three wires 12, 13 and 14 used for formation of the two

current paths are of the same material and so have the same rate of change in resistance due to the ambient temperature. The current  $I_s$  is therefore divisible at an unvarying rate in the face of temperature variations, resulting in highly accurate current detection.

11. The Hall-effect device 1 is sufficiently electrically isolated from the baseplate 2 by the insulating plate 16.

12. Noise due to external magnetic and electric disturbances is eliminated by the bottom shielding layer 17.

13. The baseplate 2 and the terminals 3, 4 and 6-11 are inexpensively fabricated from common sheet-metal punchings.

#### Second Form

FIGS. 9 and 10 show, in views similar respectively to FIGS. 1 and 8, a second preferred form of current detector according to the invention. As will be understood from a comparison of these figures, this second form differs from the first in the following respects, the other details of construction being alike in both forms:

1. The insulating plate 16, bottom shielding layer 17, metal layer 33, insulating adhesive layer 34 and conductive bonding layer 35 of the first current detector are absent from the second.

2. The baseplate 2 is bonded directly to the underside of the semiconductor substrate 23, as of gallium arsenide, via a layer 35a of a conductive bonding agent such as silver.

There being no wire 12 directly interconnecting the two current path terminals 3 and 4, the incoming current  $I_s$  is wholly directed into the conductor strip 15 and detected by the Hall-effect device 1. This second embodiment nevertheless gains all but 8-12 of the thirteen advantages set forth for the first embodiment.

#### Third Form

In FIG. 11 is shown still another preferred form of current detector according to the invention, which is similar to the FIGS. 9 and 10 embodiment except for the addition of a second shielding layer 50a. Like the second embodiment this third has the first shielding layer 50 between

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1 conductor strip 15 and semiconductor substrate 23. The second shielding  
2 layer 50a, which may be of molybdenum, is formed between insulating  
3 layer 32d and magnetic collector 51.

4 Despite the showing of FIG. 11, however, the first shielding layer  
5 50 could be omitted, provided that the device was rendered amply noise-  
6 proof by the second shielding layer 50a alone. As another modification  
7 of this FIG. 11 embodiment, the shielding layer 50a could be formed on,  
8 instead of under, the magnetic collector 51.

9 Notwithstanding the foregoing detailed disclosure, it is not desired  
10 that the present invention be limited by the exact showings of the draw-  
11 ings or by the description thereof. The following is a brief list of pos-  
12 sible modifications, alterations and adaptations of the illustrated embodi-  
13 ments that will readily suggest themselves to the specialists on the basis  
14 of this disclosure:

15 1. The semiconductor substrate 23 could be fabricated from semi-  
16 conductors such as 3-5 group compounds other than silicon or gallium ar-  
17 senide. Although the resulting substrate would be more susceptible to  
18 external magnetic fields or inductive noise, the shielding layers 17, 50 or  
19 50a would more than amply offset this shortcoming.

20 2. The insulating plate 16 and bottom shielding layer 17 could be  
21 omitted from the first embodiment, with the Hall-effect device 1 formed  
22 directly on the baseplate 2.

23 3. A Hall-voltage amplifier could be built into the same semicon-  
24 ductor substrate as was the Hall-effect device 1.

25 4. Two or more Hall-effect devices could be formed in one and  
26 the same semiconductor substrate, thereby conjointly detecting the current  
27 with higher sensitivity.

28 All these and other similar changes of the invention are intended  
29 in the foregoing disclosure. It is therefore appropriate that the invention  
30 be construed broadly and in a manner consistent with the fair meaning  
31 or proper scope of the claims which follow.

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